JSPS CAS QNERC Symposium on Nanowires and Nanodevices

March 30, 2016

O-okayama Building South-9, Room 605

Sponsored by JSPS-CAS International Bilateral Collaboration Program and QNERC, Tokyo Institute of Technology

10:50 – 11:00 Shunri Oda, Introduction

11:00 – 11:25 Buwen Cheng (IoS-CAS), Synthesis of high quality GeSn(Si) materials by sputtering

11:25 – 11:50 Chunlai Xue (IoS-CAS), Si-based GeSn alloy Epitaxy and thermal stability characterization

11:50 – 13:00 Lunch break

13:00 – 13:25 Yukio Kawano, Nano-Carbon Terahertz Sensors and Imagers

13:25 – 13:50 Tetsuo Kodera, Development of quantum information devices using group-IV semiconductor materials

13:50 – 14:15 Zhi Liu (IoS-CAS), Ge on Insulator Formed by Rapid Melting Growth

14:15 – 14:40 Chuanbo Li (IoS-CAS), Si based nano-structure for thermoelectric devices application

14:40 – 14:50 break

14:50 – 15:15 Tomohiro Noguchi, Ge-core/Si-shell nanowires for thermoelectric device application

15:15 – 15:40 Marolop Simmanullang, Ge-core/Si-shell nanowires with conformal amorphous shell thickness for high-mobility p-type field-effect transistors

15:40 – 16:05 Zhengyu Xu, Growth condition of Ge nanowires for doping

16:05 – 16:30 Takamasa Kawanago, Self-assembled monolayer-based gate dielectrics for MoS2 field-effect transistors

16:30 – 16:40 break

16:40 – 17:05 Mutsuko Hatano, Diamond Quantum Sensor

17:05 – 17:30 Ken Uchida (Keio Univ.), Deionization of dopants in silicon nanofilms

17:30 – 17:55 Simon Deleonibus (CEA/LETI), Towards the Energy Efficient, Heterogeneous Process Technology, Zero Intrinsic Variability Devices and Zero Power Era.

17:55 – 18:00 Wrap up